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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	55296
Number of I/O	97
Number of Gates	400000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p400-fgg144

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Table 2-13 • Summary of I/O Output Buffer Power (Per Pin) – Default I/O Software Settings ¹ Applicable to Standard I/O Banks

	C _{LOAD} (pF)	VCCI (V)	Static Power PDC3 (mW) ²	Dynamic Power PAC10 (µW/MHz) ³
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	35	3.3	-	431.08
3.3 V LVCMOS Wide Range ⁴	35	3.3	-	431.08
2.5 V LVCMOS	35	2.5	-	247.36
1.8 V LVCMOS	35	1.8	-	128.46
1.5 V LVCMOS (JESD8-11)	35	1.5	-	89.46

Notes:

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.

2. P_{DC3} is the static power (where applicable) measured on VCCI.

3. P_{AC10} is the total dynamic power measured on VCC and VCCI.

4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.



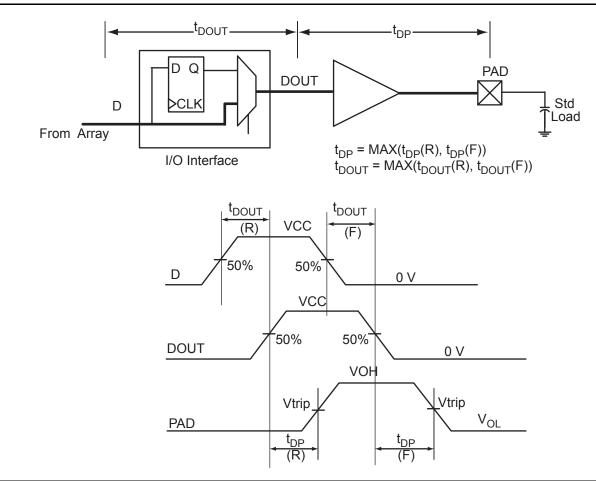


Figure 2-5 • Output Buffer Model and Delays (Example)



3.3 V LVCMOS Wide Range

Table 2-47 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

3.3 V LVCMOS Wide Range	Equiv. Software Default	v	IL	v	ІН	VOL	voн	IOL	ЮН	IOSL	IOSH	IIL ²	IIH ³
Drive Strength	Drive Strength Option ¹	Min V	Max V	Min V	Max V	Max V	Min V	μA	μA	Max mA ⁴	Max mA ⁴	µA⁵	μA ⁵
100 µA	2 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	4 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	6 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	8 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	12 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	103	109	10	10
100 µA	16 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	132	127	10	10
100 µA	24 mA	-0.3	0.8	2	3.6	0.2	VDD - 0.2	100	100	268	181	10	10

Notes:

 The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.

3. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges

4. Currents are measured at 85°C junction temperature.

5. All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

6. Software default selection highlighted in gray.

Table 2-48 • Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks

3.3 V LVCMOS Wide Range	Equiv. Software	V	L	v	ΊH	VOL	VOH	IOL	ЮН	IOSL	IOSH	IIL²	IIH ³
Drive Strength	Default Drive Strength Option ¹	Min V	Max V	Min V	Max V	Max V	Min V	μA	μA	Max mA ⁴	Max mA ⁴	μA ⁵	μ Α ⁵
100 µA	2 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	4 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	6 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	8 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	12 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	103	109	10	10
100 μA	16 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	103	109	10	10

Notes:

 The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.

3. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges

4. Currents are measured at 85°C junction temperature.

5. All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

6. Software default selection highlighted in gray.

Table 2-53 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V Applicable to Standard Plus I/O Banks

								1						T
Drive Strength	Equiv. Software Default Drive Strength Option ¹	Speed Grade	t _{dout}	t _{DP}	t _{DIN}	t _{PY}	t _{eout}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	t _{zLS}	t _{zнs}	Units
100 µA	2 mA	Std.	0.60	14.97	0.04	1.52	0.43	14.97	12.79	3.52	3.41	18.36	16.18	ns
		-1	0.51	12.73	0.04	1.29	0.36	12.73	10.88	2.99	2.90	15.62	13.77	ns
		-2	0.45	11.18	0.03	1.14	0.32	11.18	9.55	2.63	2.55	13.71	12.08	ns
100 µA	4 mA	Std.	0.60	10.36	0.04	1.52	0.43	10.36	8.93	3.99	4.24	13.75	12.33	ns
		-1	0.51	8.81	0.04	1.29	0.36	8.81	7.60	3.39	3.60	11.70	10.49	ns
		-2	0.45	7.74	0.03	1.14	0.32	7.74	6.67	2.98	3.16	10.27	9.21	ns
100 µA	6 mA	Std.	0.60	10.36	0.04	1.52	0.43	10.36	8.93	3.99	4.24	13.75	12.33	ns
		-1	0.51	8.81	0.04	1.29	0.36	8.81	7.60	3.39	3.60	11.70	10.49	ns
		-2	0.45	7.74	0.03	1.14	0.32	7.74	6.67	2.98	3.16	10.27	9.21	ns
100 µA	8 mA	Std.	0.60	7.81	0.04	1.52	0.43	7.81	6.85	4.32	4.76	11.20	10.24	ns
		-1	0.51	6.64	0.04	1.29	0.36	6.64	5.82	3.67	4.05	9.53	8.71	ns
		-2	0.45	5.83	0.03	1.14	0.32	5.83	5.11	3.22	3.56	8.36	7.65	ns
100 µA	16 mA	Std.	0.60	7.81	0.04	1.52	0.43	7.81	6.85	4.32	4.76	11.20	10.24	ns
		-1	0.51	6.64	0.04	1.29	0.36	6.64	5.82	3.67	4.05	9.53	8.71	ns
		-2	0.45	5.83	0.03	1.14	0.32	5.83	5.11	3.22	3.56	8.36	7.65	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \ \mu$ A. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

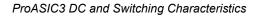




Table 2-54 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew Commercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

	Applicable to	Stanuaru i		S								
Drive Strength	Equiv. Software Default Drive Strength Option ¹	Speed Grade	t _{dout}	t _{DP}	t _{DIN}	t _{PY}	t _{eout}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
100 µA	2 mA	Std.	0.60	10.93	0.04	1.52	0.43	10.93	9.46	3.20	3.32	ns
		-1	0.51	9.29	0.04	1.29	0.36	9.29	8.04	2.72	2.82	ns
		-2	0.45	8.16	0.03	1.13	0.32	8.16	7.06	2.39	2.48	ns
100 µA	4 mA	Std.	0.60	10.93	0.04	1.52	0.43	10.93	9.46	3.20	3.32	ns
		-1	0.51	9.29	0.04	1.29	0.36	9.29	8.04	2.72	2.82	ns
		-2	0.45	8.16	0.03	1.13	0.32	8.16	7.06	2.39	2.48	ns
100 µA	6 mA	Std.	0.60	6.82	0.04	1.52	0.43	6.82	5.70	3.70	4.16	ns
		-1	0.51	5.80	0.04	1.29	0.36	5.80	4.85	3.15	3.54	ns
		-2	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns
100 µA	8 mA	Std.	0.60	6.82	0.04	1.52	0.43	6.82	5.70	3.70	4.16	ns
		-1	0.51	5.80	0.04	1.29	0.36	5.80	4.85	3.15	3.54	ns
		-2	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \ \mu$ A. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. Software default selection highlighted in gray.



1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

1.8 V LVCMOS		VIL	VIH		VOL	VOH	IOL	юн	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA ³	Max mA ³	μA ⁴	μA ⁴
2 mA	-0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI-0.45	2	2	11	9	10	10
4 mA	-0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI-0.45	4	4	22	17	10	10
6 mA	-0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI - 0.45	6	6	44	35	10	10
8 mA	-0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI-0.45	8	8	51	45	10	10
12 mA	-0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI-0.45	12	12	74	91	10	10
16 mA	-0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI-0.45	16	16	74	91	10	10

Table 2-66 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges

3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

4. Currents are measured at 85°C junction temperature.

5. Software default selection highlighted in gray.

Table 2-67 • Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O I/O Banks

1.8 V LVCMOS		VIL	VIH		VOL	VOH	IOL	ЮН	IOSL	IOSH	IIL¹	IIH ²
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA ³	Max mA ³	μA ⁴	μA ⁴
2 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	2	2	11	9	10	10
4 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4	22	17	10	10
6 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	6	6	44	35	10	10
8 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI - 0.45	8	8	44	35	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN <V CCI. Input current is larger when operating outside recommended ranges

3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

- 4. Currents are measured at 85°C junction temperature.
- 5. Software default selection highlighted in gray.



Table 2-73 • 1.8 V LVCMOS Low Slew

Commercial-Case Conditions: T _J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Plus I/O Banks

	Applicab		naara i		Danie								
Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	t _{zLS}	t _{zHS}	Units
2 mA	Std.	0.66	14.80	0.04	1.20	0.43	13.49	14.80	2.25	1.46	15.73	17.04	ns
	-1	0.56	12.59	0.04	1.02	0.36	11.48	12.59	1.91	1.25	13.38	14.49	ns
	-2	0.49	11.05	0.03	0.90	0.32	10.08	11.05	1.68	1.09	11.75	12.72	ns
4 mA	Std.	0.66	9.90	0.04	1.20	0.43	9.73	9.90	2.65	2.50	11.97	12.13	ns
	-1	0.56	8.42	0.04	1.02	0.36	8.28	8.42	2.26	2.12	10.18	10.32	ns
	-2	0.49	7.39	0.03	0.90	0.32	7.27	7.39	1.98	1.86	8.94	9.06	ns
6 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	-1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	-2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns
8 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	-1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	-2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-74 • 1.8 V LVCMOS High SlewCommercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 VApplicable to Standard I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	Units
2 mA	Std.	0.66	11.21	0.04	1.20	0.43	8.53	11.21	1.99	1.21	ns
	-1	0.56	9.54	0.04	1.02	0.36	7.26	9.54	1.69	1.03	ns
	-2	0.49	8.37	0.03	0.90	0.32	6.37	8.37	1.49	0.90	ns
4 mA	Std.	0.66	6.34	0.04	1.20	0.43	5.38	6.34	2.41	2.48	ns
	-1	0.56	5.40	0.04	1.02	0.36	4.58	5.40	2.05	2.11	ns
	-2	0.49	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns

Notes:

1. Software default selection highlighted in gray.



DC Parameter	Description	Min.	Тур.	Max.	Units
VCCI	Supply Voltage	2.375	2.5	2.625	V
VOL	Output Low Voltage	0.9	1.075	1.25	V
VOH	Output High Voltage	1.25	1.425	1.6	V
IOL ¹	Output Lower Current	0.65	0.91	1.16	mA
IOH ¹	Output High Current	0.65	0.91	1.16	mA
VI	Input Voltage	0		2.925	V
IIH ^{2,3}	Input High Leakage Current			10	μA
IIL ^{2,4}	Input Low Leakage Current			10	μA
VODIFF	Differential Output Voltage	250	350	450	mV
VOCM	Output Common Mode Voltage	1.125	1.25	1.375	V
VICM	Input Common Mode Voltage	0.05	1.25	2.35	V
VIDIFF	Input Differential Voltage	100	350		mV

Table 2-90 • LVDS Minimum and Maximum DC Input and Output Levels

Notes:

1. IOL/IOH defined by VODIFF/(Resistor Network)

2. Currents are measured at 85°C junction temperature.

- 3. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN <VCCI. Input current is larger when operating outside recommended ranges.
- 4. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN <VIL.

Table 2-91 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)
1.075	1.325	Cross point

Note: *Measuring point = $V_{trip.}$ See Table 2-22 on page 2-22 for a complete table of trip points.

Timing Characteristics

Table 2-92 • LVDS

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	Units
Std.	0.66	1.83	0.04	1.60	ns
-1	0.56	1.56	0.04	1.36	ns
-2	0.49	1.37	0.03	1.20	ns



Embedded SRAM and FIFO Characteristics

SRAM

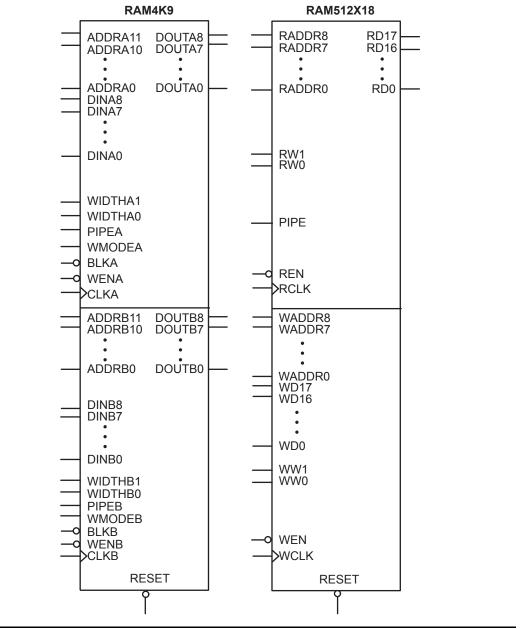


Figure 2-30 • RAM Models



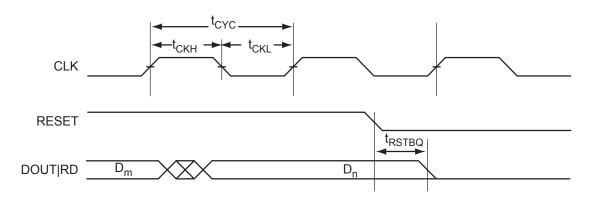


Figure 2-35 • RAM Reset. Applicable to Both RAM4K9 and RAM512x18.



Parameter	Description	-2	-1	Std.	Units
t _{AS}	Address setup time	0.25	0.28	0.33	ns
t _{AH}	Address hold time	0.00	0.00	0.00	ns
t _{ENS}	REN, WEN setup time	0.13	0.15	0.17	ns
t _{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t _{DS}	Input data (WD) setup time	0.18	0.21	0.25	ns
t _{DH}	Input data (WD) hold time	0.00	0.00	0.00	ns
t _{CKQ1}	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
t _{CKQ2}	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
t _{C2CRWH} 1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
t _{C2CWRH} 1	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.59	0.50	0.44	ns
t _{RSTBQ}	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
t _{REMRSTB}	RESET removal	0.29	0.33	0.38	ns
t _{RECRSTB}	RESET recovery	1.50	1.71	2.01	ns
t _{MPWRSTB}	RESET minimum pulse width	0.21	0.24	0.29	ns
t _{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F _{MAX}	Maximum frequency	310	272	231	MHz

Table 2-117 • RAM512X18

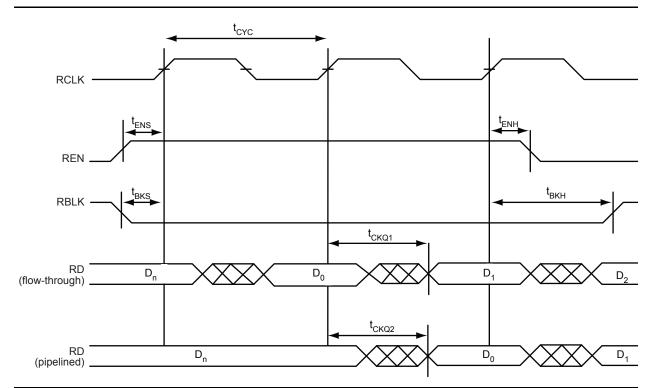
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

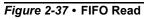
Notes:

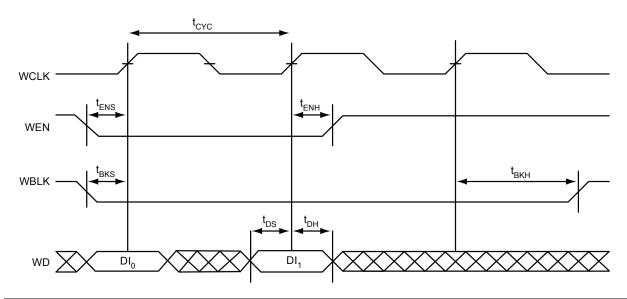
1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.

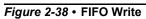


Timing Waveforms











	PQ208		PQ208	PQ208	
Pin Number	A3P125 Function	Pin Number	A3P125 Function	Pin Number	A3P125 Function
1	GND	37	IO116RSB1	73	IO92RSB1
2	GAA2/IO67RSB1	38	IO115RSB1	74	IO91RSB1
3	IO68RSB1	39	NC	75	IO90RSB1
4	GAB2/IO69RSB1	40	VCCIB1	76	IO89RSB1
5	IO132RSB1	41	GND	77	IO88RSB1
6	GAC2/IO131RSB1	42	IO114RSB1	78	IO87RSB1
7	NC	43	IO113RSB1	79	IO86RSB1
8	NC	44	GEC1/IO112RSB1	80	IO85RSB1
9	IO130RSB1	45	GEC0/IO111RSB1	81	GND
10	IO129RSB1	46	GEB1/IO110RSB1	82	IO84RSB1
11	NC	47	GEB0/IO109RSB1	83	IO83RSB1
12	IO128RSB1	48	GEA1/IO108RSB1	84	IO82RSB1
13	NC	49	GEA0/IO107RSB1	85	IO81RSB1
14	NC	50	VMV1	86	IO80RSB1
15	NC	51	GNDQ	87	IO79RSB1
16	VCC	52	GND	88	VCC
17	GND	53	NC	89	VCCIB1
18	VCCIB1	54	NC	90	IO78RSB1
19	IO127RSB1	55	GEA2/IO106RSB1	91	IO77RSB1
20	NC	56	GEB2/IO105RSB1	92	IO76RSB1
21	GFC1/IO126RSB1	57	GEC2/IO104RSB1	93	IO75RSB1
22	GFC0/IO125RSB1	58	IO103RSB1	94	IO74RSB1
23	GFB1/IO124RSB1	59	IO102RSB1	95	IO73RSB1
24	GFB0/IO123RSB1	60	IO101RSB1	96	GDC2/IO72RSB1
25	VCOMPLF	61	IO100RSB1	97	GND
26	GFA0/IO122RSB1	62	VCCIB1	98	GDB2/IO71RSB1
27	VCCPLF	63	IO99RSB1	99	GDA2/IO70RSB1
28	GFA1/IO121RSB1	64	IO98RSB1	100	GNDQ
29	GND	65	GND	101	ТСК
30	GFA2/IO120RSB1	66	IO97RSB1	102	TDI
31	NC	67	IO96RSB1	103	TMS
32	GFB2/IO119RSB1	68	IO95RSB1	104	VMV1
33	NC	69	IO94RSB1	105	GND
34	GFC2/IO118RSB1	70	IO93RSB1	106	VPUMP
35	IO117RSB1	71	VCC	107	NC
36	NC	72	VCCIB1	108	TDO

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Package Pin Assignments

F	G144	F	G144	FG144	
Pin Number	A3P125 Function	Pin Number	A3P125 Function	Pin Number	A3P125 Function
A1	GNDQ	D1	IO128RSB1	G1	GFA1/IO121RSB1
A2	VMV0	D2	IO129RSB1	G2	GND
A3	GAB0/IO02RSB0	D3	IO130RSB1	G3	VCCPLF
A4	GAB1/IO03RSB0	D4	GAA2/IO67RSB1	G4	GFA0/IO122RSB1
A5	IO11RSB0	D5	GAC0/IO04RSB0	G5	GND
A6	GND	D6	GAC1/IO05RSB0	G6	GND
A7	IO18RSB0	D7	GBC0/IO35RSB0	G7	GND
A8	VCC	D8	GBC1/IO36RSB0	G8	GDC1/IO61RSB0
A9	IO25RSB0	D9	GBB2/IO43RSB0	G9	IO48RSB0
A10	GBA0/IO39RSB0	D10	IO28RSB0	G10	GCC2/IO59RSB0
A11	GBA1/IO40RSB0	D11	IO44RSB0	G11	IO47RSB0
A12	GNDQ	D12	GCB1/IO53RSB0	G12	GCB2/IO58RSB0
B1	GAB2/IO69RSB1	E1	VCC	H1	VCC
B2	GND	E2	GFC0/IO125RSB1	H2	GFB2/IO119RSB1
B3	GAA0/IO00RSB0	E3	GFC1/IO126RSB1	H3	GFC2/IO118RSB1
B4	GAA1/IO01RSB0	E4	VCCIB1	H4	GEC1/IO112RSB1
B5	IO08RSB0	E5	IO68RSB1	H5	VCC
B6	IO14RSB0	E6	VCCIB0	H6	IO50RSB0
B7	IO19RSB0	E7	VCCIB0	H7	IO60RSB0
B8	IO22RSB0	E8	GCC1/IO51RSB0	H8	GDB2/IO71RSB1
B9	GBB0/IO37RSB0	E9	VCCIB0	Н9	GDC0/IO62RSB0
B10	GBB1/IO38RSB0	E10	VCC	H10	VCCIB0
B11	GND	E11	GCA0/IO56RSB0	H11	IO49RSB0
B12	VMV0	E12	IO46RSB0	H12	VCC
C1	IO132RSB1	F1	GFB0/IO123RSB1	J1	GEB1/IO110RSB1
C2	GFA2/IO120RSB1	F2	VCOMPLF	J2	IO115RSB1
C3	GAC2/IO131RSB1	F3	GFB1/IO124RSB1	J3	VCCIB1
C4	VCC	F4	IO127RSB1	J4	GEC0/IO111RSB1
C5	IO10RSB0	F5	GND	J5	IO116RSB1
C6	IO12RSB0	F6	GND	J6	IO117RSB1
C7	IO21RSB0	F7	GND	J7	VCC
C8	IO24RSB0	F8	GCC0/IO52RSB0	J8	ТСК
C9	IO27RSB0	F9	GCB0/IO54RSB0	J9	GDA2/IO70RSB1
C10	GBA2/IO41RSB0	F10	GND	J10	TDO
C11	IO42RSB0	F11	GCA1/IO55RSB0	J11	GDA1/IO65RSB0
C12	GBC2/IO45RSB0	F12	GCA2/IO57RSB0	J12	GDB1/IO63RSB0

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Package Pin Assignments

	FG256		FG256	FG256	
Pin Number	A3P250 Function	Pin Number	A3P250 Function	Pin Number	A3P250 Function
G13	GCC1/IO48PPB1	K1	GFC2/IO105PDB3	M5	VMV3
G14	IO47NPB1	K2	IO107NPB3	M6	VCCIB2
G15	IO54PDB1	K3	IO104PPB3	M7	VCCIB2
G16	IO54NDB1	K4	NC	M8	NC
H1	GFB0/IO109NPB3	K5	VCCIB3	M9	IO74RSB2
H2	GFA0/IO108NDB3	K6	VCC	M10	VCCIB2
H3	GFB1/IO109PPB3	K7	GND	M11	VCCIB2
H4	VCOMPLF	K8	GND	M12	VMV2
H5	GFC0/IO110NPB3	K9	GND	M13	NC
H6	VCC	K10	GND	M14	GDB1/IO59UPB1
H7	GND	K11	VCC	M15	GDC1/IO58UDB1
H8	GND	K12	VCCIB1	M16	IO56NDB1
H9	GND	K13	IO52NPB1	N1	IO103NDB3
H10	GND	K14	IO55RSB1	N2	IO101PPB3
H11	VCC	K15	IO53NPB1	N3	GEC1/IO100PPB3
H12	GCC0/IO48NPB1	K16	IO51NDB1	N4	NC
H13	GCB1/IO49PPB1	L1	IO105NDB3	N5	GNDQ
H14	GCA0/IO50NPB1	L2	IO104NPB3	N6	GEA2/IO97RSB2
H15	NC	L3	NC	N7	IO86RSB2
H16	GCB0/IO49NPB1	L4	IO102RSB3	N8	IO82RSB2
J1	GFA2/IO107PPB3	L5	VCCIB3	N9	IO75RSB2
J2	GFA1/IO108PDB3	L6	GND	N10	IO69RSB2
J3	VCCPLF	L7	VCC	N11	IO64RSB2
J4	IO106NDB3	L8	VCC	N12	GNDQ
J5	GFB2/IO106PDB3	L9	VCC	N13	NC
J6	VCC	L10	VCC	N14	VJTAG
J7	GND	L11	GND	N15	GDC0/IO58VDB1
J8	GND	L12	VCCIB1	N16	GDA1/IO60UDB1
J9	GND	L13	GDB0/IO59VPB1	P1	GEB1/IO99PDB3
J10	GND	L14	IO57VDB1	P2	GEB0/IO99NDB3
J11	VCC	L15	IO57UDB1	P3	NC
J12	GCB2/IO52PPB1	L16	IO56PDB1	P4	NC
J13	GCA1/IO50PPB1	M1	IO103PDB3	P5	IO92RSB2
J14	GCC2/IO53PPB1	M2	NC	P6	IO89RSB2
J15	NC	M3	IO101NPB3	P7	IO85RSB2
J16	GCA2/IO51PDB1	M4	GEC0/IO100NPB3	P8	IO81RSB2

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Package Pin Assignments

	FG484
Pin Number	A3P400 Function
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB1
AA1	GND
AA2	VCCIB3
AA3	NC
AA4	NC
AA5	NC
AA6	NC
AA7	NC
AA8	NC
AA9	NC
AA10	NC
AA11	NC
AA12	NC
AA13	NC
AA14	NC
AA15	NC
AA16	NC
AA17	NC
AA18	NC
AA19	NC
AA20	NC
AA21	VCCIB1
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB2
AB4	NC
AB5	NC
AB6	IO121RSB2

	FG484			
Pin Number	A3P400 Function			
AB7	IO119RSB2			
AB8	IO114RSB2			
AB9	IO109RSB2			
AB10	NC			
AB11	NC			
AB12	IO104RSB2			
AB13	IO103RSB2			
AB14	NC			
AB15	NC			
AB16	IO91RSB2			
AB17	IO90RSB2			
AB18	NC			
AB19	NC			
AB20	VCCIB2			
AB21	GND			
AB22	GND			



5 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each version of the ProASIC3 datasheet.

Revision	Changes	Page
Revision 18 (March 2016)	Updated 3.3 V DC supply voltage's maximum Commercial and Industrial values from 3.3 V to 3.6 V in Table 2-2 (SAR 72693).	2-2
	Added reference of Package Mechanical Drawings document in all package pin assignment notes (76833).	NA
Revision 17	Removed PQFP embedded heat spreader info. from Table 2-5 (SAR 52320).	2-6
(June 2015)	Updated "VCCIBx I/O Supply Voltage" (SAR 43323).	3-1
Revision 16 (December 2014)	Updated "ProASIC3 Ordering Information". Interchanged the positions of Y- Security Feature and I- Application (Temperature Range) (SAR 61079). Added Note "Only devices with package size greater than or equal to 5x5 are supported".	1-IV
	Updated Table Note (2) in Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature so that the Table Note is not applicable for Maximum Storage Temperature T_{STG} (SAR 54297).	2-3
	Added values for Drive strength 2 mA in Table 2-41 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew, Table 2-42 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew, Table 2-43 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew, and Table 2-44 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew (SAR 57184).	2-34, 2-35, 2-36, 2-37
	Added Figure 2-1 • High-Temperature Data Retention (HTR) (SAR 45466).	2-3
	Updates made to maintain the style and consistency of the document.	NA
Revision 15 (July 2014)	Added corner pad table note (3) to "QN132 – Bottom View" (SAR 47442).	4-6
	Ambient temperature removed in Table 2-2, table notes and "ProASIC3 Ordering Information" figure were modified (SAR 48343).	2-2 1-IV
	Other updates were made to maintain the style and consistency of the datasheet.	NA
Revision 14 (April 2014)	Note added for the discontinuance of QN132 package to the following tables and section: "ProASIC3 Devices", "I/Os Per Package 1", "ProASIC3 FPGAs Package Sizes Dimensions" and "QN132 – Bottom View" section (SAR 55118).	I, III, 4-6



Datasheet Information

Revision	Changes	Page
Revision 10 (continued)	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-28 • I/O Output Buffer Maximum Resistances1 through Table 2-30 • I/O Output Buffer Maximum Resistances1 was replaced by "Same as regular 3.3 V" (SAR 33852).	2-26 to 2-28
	The equations in the notes for Table 2-31 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 32470).	2-28
	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-32 • I/O Short Currents IOSH/IOSL through Table 2-34 • I/O Short Currents IOSH/IOSL was replaced by "Same as regular 3.3 V LVCMOS" (SAR 33852).	2-29 to 2-31
	In the "3.3 V LVCMOS Wide Range" section, values were added to Table 2-47 through Table 2-49 for IOSL and IOSH, replacing "TBD" (SAR 33852).	2-39 to 2-40
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 24916): "It uses a 5 V-tolerant input buffer and push-pull output buffer."	2-47
	The table notes were revised for Table 2-90 • LVDS Minimum and Maximum DC Input and Output Levels (SAR 33859).	2-66
	Values were added for $F_{DDRIMAX}$ and F_{DDOMAX} in Table 2-102 • Input DDR Propagation Delays and Table 2-104 • Output DDR Propagation Delays (SAR 23919).	2-78, 2-80
	Table 2-115 • ProASIC3 CCC/PLL Specification was updated. A note was added to indicate that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 25705).	2-90
	The following figures were deleted (SAR 29991). Reference was made to a new application note, <i>Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs</i> , which covers these cases in detail (SAR 21770).	2-92,
	Figure 2-34 • Write Access after Write onto Same Address Figure 2-35 • Read Access after Write onto Same Address Figure 2-35 • Read Access after Write onto Same Address	2-94, 2-99 2-102
	The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-39 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SARs 29991, 30510).	
	The "Pin Descriptions" chapter has been added (SAR 21642).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in <i>Package Mechanical Drawings</i> (SAR 27395).	4-1
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "ProASIC3 Device Status" table on page IV indicates the status for each device in the device family.	N/A

Revision	Changes	Page
Revision 9 (Oct 2009) Product Brief v1.3	The CS121 package was added to table under "Features and Benefits" section, the "I/Os Per Package 1" table, Table 1 • ProASIC3 FPGAs Package Sizes Dimensions, "ProASIC3 Ordering Information", and the "Temperature Grade Offerings" table.	I – IV
	"ProASIC3 Ordering Information" was revised to include the fact that some RoHS compliant packages are halogen-free.	IV
Packaging v1.5	The "CS121 – Bottom View" figure and pin table for A3P060 are new.	4-15
Revision 8 (Aug 2009) Product Brief v1.2	All references to M7 devices (CoreMP7) and speed grade –F were removed from this document.	N/A
	Table 1-1 I/O Standards supported is new.	1-7
	The I/Os with Advanced I/O Standards section was revised to add definitions of hot-swap and cold-sparing.	1-7
DC and Switching Characteristics v1.4	$3.3~\rm V$ LVCMOS and $1.2~\rm V$ LVCMOS Wide Range support was added to the datasheet. This affects all tables that contained $3.3~\rm V$ LVCMOS and $1.2~\rm V$ LVCMOS data.	N/A
	$\rm I_{\rm IL}$ and $\rm I_{\rm IH}$ input leakage current information was added to all "Minimum and Maximum DC Input and Output Levels" tables.	N/A
	-F was removed from the datasheet. The speed grade is no longer supported.	N/A
	The notes in Table 2-2 • Recommended Operating Conditions 1 were updated.	2-2
	Table 2-4 • Overshoot and Undershoot Limits 1 was updated.	2-3
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays was updated.	2-6
	In Table 2-116 • RAM4K9, the following specifications were removed: t _{WRO} t _{CCKH}	2-96
	In Table 2-117 • RAM512X18, the following specifications were removed: t _{WRO} t _{CCKH}	2-97
	In the title of Table 2-74 • 1.8 V LVCMOS High Slew, VCCI had a typo. It was changed from 3.0 V to 1.7 V.	2-58
Revision 7 (Feb 2009) Product Brief v1.1	The "Advanced I/O" section was revised to add a bullet regarding wide range power supply voltage support.	I
	The table under "Features and Benefits" section, was updated to include a value for typical equivalent macrocells for A3P250.	I
	The QN48 package was added to the following tables: the table under "Features and Benefits" section, "I/Os Per Package 1" "ProASIC3 FPGAs Package Sizes Dimensions", and "Temperature Grade Offerings".	N/A
	The number of singled-ended I/Os for QN68 was added to the "I/Os Per Package 1" table.	
	The Wide Range I/O Support section is new.	1-7
Revision 6 (Dec 2008)	The "QN48 – Bottom View" section is new.	4-1
Packaging v1.4	The "QN68" pin table for A3P030 is new.	4-5



Datasheet Information

Revision	Changes	Page
Revision 5 (Aug 2008) DC and Switching Characteristics v1.3	TJ, Maximum Junction Temperature, was changed to 100° from 110° in the "Thermal Characteristics" section and EQ 1. The calculated result of Maximum Power Allowed has thus changed to 1.463 W from 1.951 W.	2-6
	Values for the A3P015 device were added to Table 2-7 • Quiescent Supply Current Characteristics.	2-7
	Values for the A3P015 device were added to Table 2-14 • Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices. P_{AC14} was removed. Table 2-15 • Different Components Contributing to the Static Power Consumption in ProASIC3 Devices is new.	2-11, 2-12
	The "PLL Contribution—PPLL" section was updated to change the P _{PLL} formula from $P_{AC13} + P_{AC14} * F_{CLKOUT}$ to $P_{DC4} + P_{AC13} * F_{CLKOUT}$.	2-14
	Both fall and rise values were included for $t_{\mbox{DDRISUD}}$ and $t_{\mbox{DDRIHD}}$ in Table 2-102 \bullet Input DDR Propagation Delays.	2-78
	Table 2-107 • A3P015 Global Resource is new.	2-86
	The typical value for Delay Increments in Programmable Delay Blocks was changed from 160 to 200 in Table 2-115 • ProASIC3 CCC/PLL Specification.	2-90
Revision 4 (Jun 2008) DC and Switching Characteristics v1.2	Table note references were added to Table 2-2 • Recommended Operating Conditions 1, and the order of the table notes was changed.	2-2
	The title for Table 2-4 • Overshoot and Undershoot Limits 1 was modified to remove "as measured on quiet I/Os." Table note 1 was revised to remove "estimated SSO density over cycles." Table note 2 was revised to remove "refers only to overshoot/undershoot limits for simultaneous switching I/Os."	2-3
	The "Power per I/O Pin" section was updated to include 3 additional tables pertaining to input buffer power and output buffer power.	2-7
	Table 2-29 • I/O Output Buffer Maximum Resistances 1 was revised to include values for 3.3 V PCI/PCI-X.	2-27
	Table 2-90 • LVDS Minimum and Maximum DC Input and Output Levels was updated.	2-66
Revision 3 (Jun 2008) Packaging v1.3	Pin numbers were added to the "QN68 – Bottom View" package diagram. Note 2 was added below the diagram.	4-3
	The "QN132 – Bottom View" package diagram was updated to include D1 to D4. In addition, note 1 was changed from top view to bottom view, and note 2 is new.	4-6
Revision 2 (Feb 2008) Product Brief v1.0	This document was divided into two sections and given a version number, starting at v1.0. The first section of the document includes features, benefits, ordering information, and temperature and speed grade offerings. The second section is a device family overview.	N/A
	This document was updated to include A3P015 device information. QN68 is a new package that was added because it is offered in the A3P015. The following sections were updated:	N/A
	"Features and Benefits"	
	"ProASIC3 Ordering Information"	
	"Temperature Grade Offerings"	
	"ProASIC3 Flash Family FPGAs"	
	"A3P015 and A3P030" note	
	Introduction and Overview (NA)	